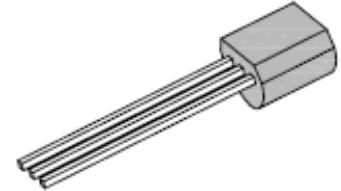


## Small Signal Darlington Transistors (NPN)

### Features

- NPN Silicon Planar Epitaxial Darlington Transistors
- RoHS Compliance



TO-92



### Mechanical Data

|                   |                                         |
|-------------------|-----------------------------------------|
| <b>Case:</b>      | TO-92, Plastic Package                  |
| <b>Terminals:</b> | Solderable per MIL-STD-202G, Method 208 |
| <b>Weight:</b>    | 0.18 gram                               |

### Maximum Ratings ( $T_{Ambient}=25^{\circ}C$ unless noted otherwise)

| Symbol                                | Description                                      | MPSA13      | MPSA14 | Unit            |
|---------------------------------------|--------------------------------------------------|-------------|--------|-----------------|
| <b>V<sub>CEO</sub></b>                | Collector-Emitter Voltage                        | 30          |        | V               |
| <b>V<sub>CBO</sub></b>                | Collector-Base Voltage                           | 30          |        | V               |
| <b>V<sub>EBO</sub></b>                | Emitter-Base Voltage                             | 10          |        | V               |
| <b>I<sub>C</sub></b>                  | Collector Current Continuous                     | 500         |        | mA              |
| <b>P<sub>D</sub></b>                  | Power Dissipation at $T_A=25^{\circ}C$           | 625         |        | mW              |
|                                       | Derate above $25^{\circ}C$                       | 5.0         |        | mW/ $^{\circ}C$ |
| <b>P<sub>D</sub></b>                  | Power Dissipation at $T_C=25^{\circ}C$           | 1.5         |        | W               |
|                                       | Derate above $25^{\circ}C$                       | 12          |        | mW/ $^{\circ}C$ |
| <b>R<sub>θJA</sub></b>                | Thermal Resistance Junction to Ambient Air       | 200         |        | $^{\circ}C/W$   |
| <b>R<sub>θJC</sub></b>                | Thermal Resistance Junction to Case              | 83.3        |        | $^{\circ}C/W$   |
| <b>T<sub>J</sub>, T<sub>STG</sub></b> | Operation and Storage Junction Temperature Range | -55 to +150 |        | $^{\circ}C$     |

# Small Signal Darlington Transistors (NPN)

## MPSA13/MPSA14

### Electrical Characteristics ( $T_{Ambient}=25^{\circ}C$ unless noted otherwise)

| Symbol                      | Description                          | MPSA13 |      | MPSA14 |      | Unit | Conditions                                             |
|-----------------------------|--------------------------------------|--------|------|--------|------|------|--------------------------------------------------------|
|                             |                                      | Min.   | Max. | Min.   | Max. |      |                                                        |
| <b>V<sub>CEO</sub></b>      | Collector-Emitter Voltage            | 30     | -    | 30     | -    | V    | I <sub>C</sub> =100μA, I <sub>B</sub> =0               |
| <b>I<sub>CBO</sub></b>      | Collector Cut-Off Current            | -      | 100  | -      | 100  | nA   | V <sub>CB</sub> =30V, I <sub>E</sub> =0                |
| <b>I<sub>EBO</sub></b>      | Emitter Cut-Off Current              | -      | 100  | -      | 100  | nA   | V <sub>EB</sub> =10V, I <sub>C</sub> =0                |
| <b>V<sub>CE(sat)</sub>*</b> | Collector Emitter Saturation Voltage | -      | 1.5  | -      | 1.5  | V    | I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA           |
| <b>V<sub>BE(on)</sub>*</b>  | Base Emitter On Voltage              | -      | 2.0  | -      | 2.0  | V    | I <sub>C</sub> =100mA, V <sub>CE</sub> =5V             |
| <b>h<sub>FE</sub>*</b>      | D.C. Current Gain                    | 5000   | -    | 10000  | -    |      | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA              |
|                             |                                      | 10000  | -    | 20000  | -    |      | V <sub>CE</sub> =5V, I <sub>C</sub> =100mA             |
| <b>f<sub>T</sub>**</b>      | Current Gain-Bandwidth Product       | 125    | -    | 125    | -    | MHz  | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA,<br>f=100MHz |

\*Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.

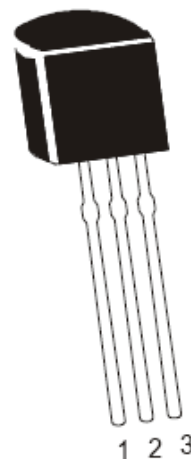
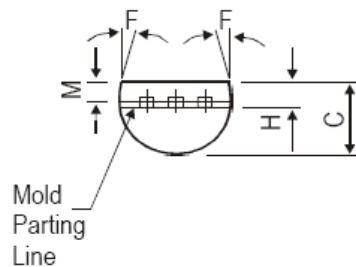
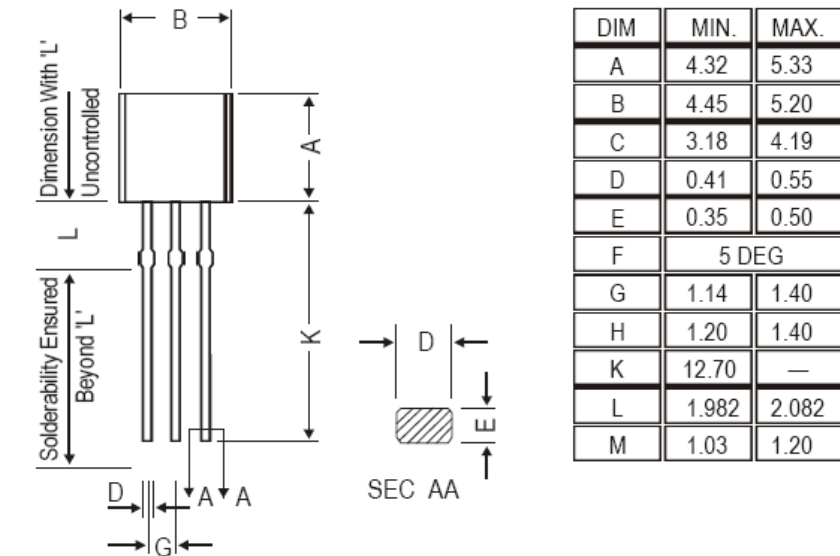
\*\* $f_T = |h_{fe}| \cdot f_{test}$ .

# Small Signal Darlington Transistors (NPN)

## MPSA13/MPSA14

Dimensions in mm

TO-92



### PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

# Small Signal Darlington Transistors (NPN)

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## MPSA13/MPSA14

### How to contact us

#### **USA HEADQUARTERS**

28040 WEST HARRISON PARKWAY, VALENCIA, CA 91355-4162

Tel: (800)-TAITRON (800)-824-8766 (661)-257-6060

Fax: (800)-TAITFAX (800)-824-8329 (661)-257-6415

Email: [taitron@taitroncomponents.com](mailto:taitron@taitroncomponents.com)

Http://[www.taitroncomponents.com](http://www.taitroncomponents.com)

#### **TAITRON COMPONENTS INCORPORATED TAIWAN BRANCH**

6F., NO.190, SEC. 2, ZHONGXING RD., XINDIAN DIST., NEW TAIPEI CITY 23146, TAIWAN R.O.C.

Tel: 886-2-2913-6238

Fax: 886-2-2913-6239

#### **TAITRON COMPONENT TECHNOLOG SHANGHAI CORPORATION**

SUITE 1503, METROBANK PLAZA, 1160 WEST YAN'AN ROAD, SHANGHAI, 200052, CHINA

Tel: +86-21-5424-9942

Fax: +86-21-2302-5027